



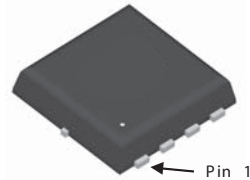
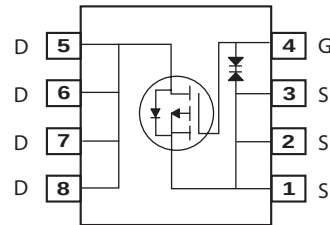
## P-Channel Enhancement Mode Field Effect Transistor

### PRODUCT SUMMARY

| V <sub>DSS</sub> | I <sub>D</sub> | R <sub>DS(ON)</sub> (mΩ) Max |
|------------------|----------------|------------------------------|
| -30V             | -8A            | 12.5 @ V <sub>GS</sub> =-10V |
|                  |                | 18 @ V <sub>GS</sub> =-4.5V  |

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.

**TSON 3.3 x 3.3**

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

| Symbol                            | Parameter                                        | Limit                | Units |
|-----------------------------------|--------------------------------------------------|----------------------|-------|
| V <sub>DS</sub>                   | Drain-Source Voltage                             | -30                  | V     |
| V <sub>GS</sub>                   | Gate-Source Voltage                              | ±20                  | V     |
| I <sub>D</sub>                    | Drain Current-Continuous <sup>a c</sup>          | T <sub>A</sub> =25°C | -8    |
|                                   |                                                  | T <sub>A</sub> =70°C | -6.4  |
| I <sub>DM</sub>                   | -Pulsed <sup>c</sup>                             | -46                  | A     |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy <sup>d</sup>       | 30                   | mJ    |
| P <sub>D</sub>                    | Maximum Power Dissipation <sup>a</sup>           | T <sub>A</sub> =25°C | 1.67  |
|                                   |                                                  | T <sub>A</sub> =70°C | 1.07  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating Junction and Storage Temperature Range | -55 to 150           | °C    |

### THERMAL CHARACTERISTICS

|                  |                                         |    |      |
|------------------|-----------------------------------------|----|------|
| R <sub>θJA</sub> | Thermal Resistance, Junction-to-Ambient | 75 | °C/W |
|------------------|-----------------------------------------|----|------|

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

| Symbol                                 | Parameter                        | Conditions                                                                                        | Min  | Typ  | Max  | Units |
|----------------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------|------|------|------|-------|
| OFF CHARACTERISTICS                    |                                  |                                                                                                   |      |      |      |       |
| BV <sub>DSS</sub>                      | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA                                                      | -30  |      |      | V     |
| I <sub>DSS</sub>                       | Zero Gate Voltage Drain Current  | V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V                                                       |      |      | -1   | uA    |
| I <sub>GSS</sub>                       | Gate-Body Leakage Current        | V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V                                                      |      |      | ±10  | uA    |
| ON CHARACTERISTICS                     |                                  |                                                                                                   |      |      |      |       |
| V <sub>GS(th)</sub>                    | Gate Threshold Voltage           | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA                                         | -1.0 | -1.6 | -3.0 | V     |
| R <sub>DS(ON)</sub>                    | Drain-Source On-State Resistance | V <sub>GS</sub> =-10V , I <sub>D</sub> =-4A                                                       |      | 10   | 12.5 | m ohm |
|                                        |                                  | V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A                                                      |      | 13   | 18   | m ohm |
| g <sub>FS</sub>                        | Forward Transconductance         | V <sub>DS</sub> =-10V , I <sub>D</sub> =-4A                                                       |      | 24   |      | S     |
| DYNAMIC CHARACTERISTICS <sup>b</sup>   |                                  |                                                                                                   |      |      |      |       |
| C <sub>ISS</sub>                       | Input Capacitance                | V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V<br>f=1.0MHz                                             |      | 3545 |      | pF    |
| C <sub>OSS</sub>                       | Output Capacitance               |                                                                                                   |      | 394  |      | pF    |
| C <sub>RSS</sub>                       | Reverse Transfer Capacitance     |                                                                                                   |      | 289  |      | pF    |
| SWITCHING CHARACTERISTICS <sup>b</sup> |                                  |                                                                                                   |      |      |      |       |
| t <sub>D(ON)</sub>                     | Turn-On Delay Time               | V <sub>DD</sub> =-15V<br>I <sub>D</sub> =-1A<br>V <sub>GS</sub> =-10V<br>R <sub>GEN</sub> = 6 ohm |      | 58   |      | ns    |
| t <sub>r</sub>                         | Rise Time                        |                                                                                                   |      | 50   |      | ns    |
| t <sub>D(OFF)</sub>                    | Turn-Off Delay Time              |                                                                                                   |      | 176  |      | ns    |
| t <sub>f</sub>                         | Fall Time                        |                                                                                                   |      | 45   |      | ns    |
| Q <sub>g</sub>                         | Total Gate Charge                | V <sub>DS</sub> =-15V,I <sub>D</sub> =-4A,V <sub>GS</sub> =-10V                                   |      | 59   |      | nC    |
|                                        |                                  | V <sub>DS</sub> =-15V,I <sub>D</sub> =-4A,V <sub>GS</sub> =-4.5V                                  |      | 28   |      | nC    |
| Q <sub>gs</sub>                        | Gate-Source Charge               | V <sub>DS</sub> =-15V,I <sub>D</sub> =-4A,                                                        |      | 5    |      | nC    |
| Q <sub>gd</sub>                        | Gate-Drain Charge                | V <sub>GS</sub> =-10V                                                                             |      | 14   |      | nC    |
| DRAIN-SOURCE DIODE CHARACTERISTICS     |                                  |                                                                                                   |      |      |      |       |
| V <sub>SD</sub>                        | Diode Forward Voltage            | V <sub>GS</sub> =0V,I <sub>S</sub> =-1A                                                           |      | -0.8 | -1.2 | V     |

**Notes**

- a. Surface Mounted on FR4 Board of 1 inch<sup>2</sup>, 1oz.  
b. Guaranteed by design, not subject to production testing.  
c. Drain current limited by maximum junction temperature.  
d. Starting  $T_J=25^{\circ}\text{C}$ ,  $L=0.5\text{mH}$ ,  $V_{DD}=20V$ . (See Figure13)

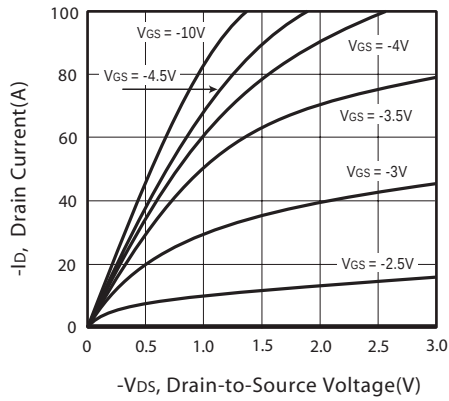


Figure 1. Output Characteristics

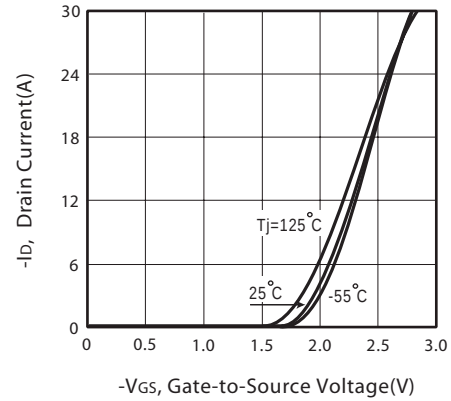


Figure 2. Transfer Characteristics

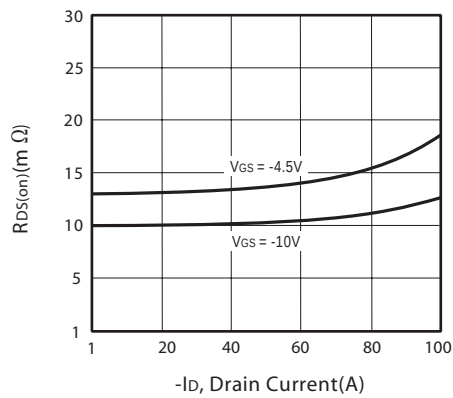


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

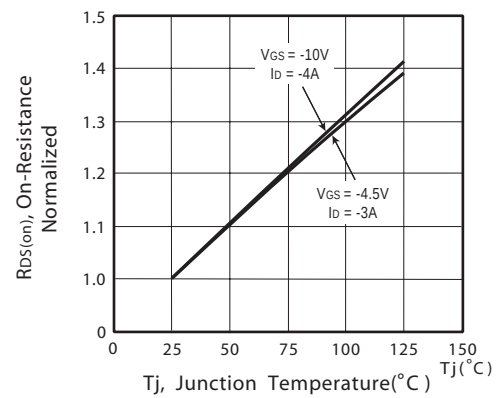


Figure 4. On-Resistance Variation with Drain Current and Temperature

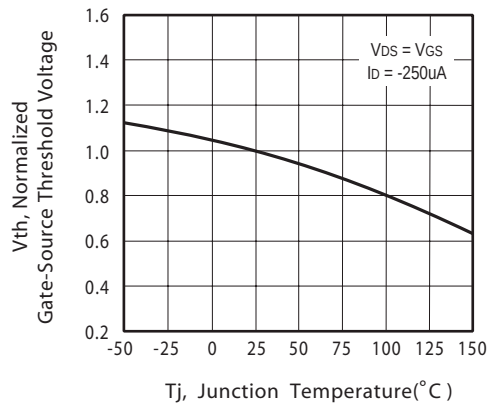


Figure 5. Gate Threshold Variation with Temperature

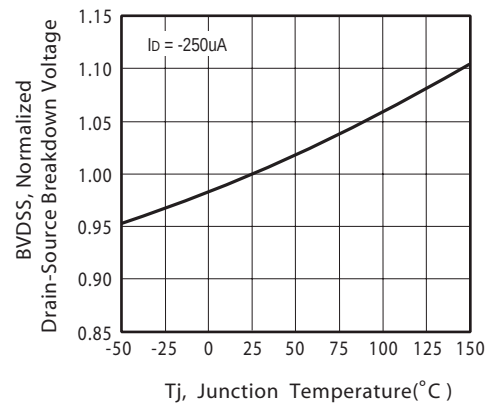
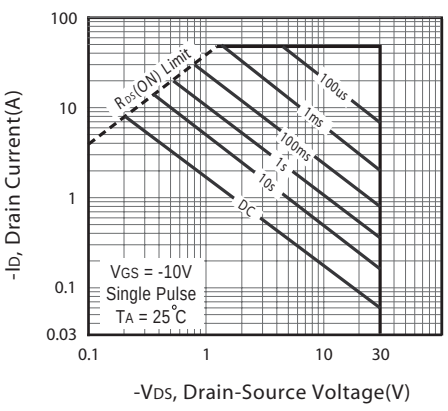
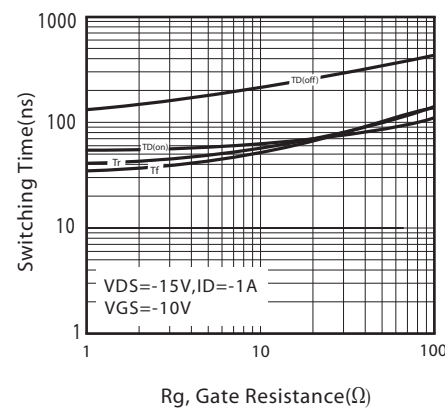
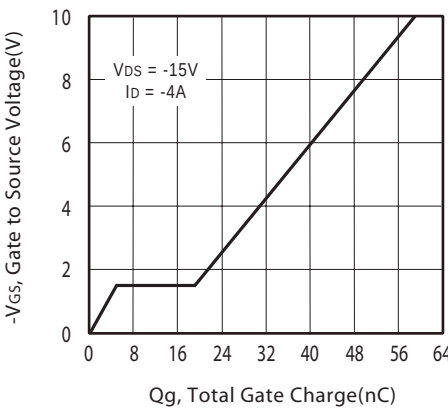
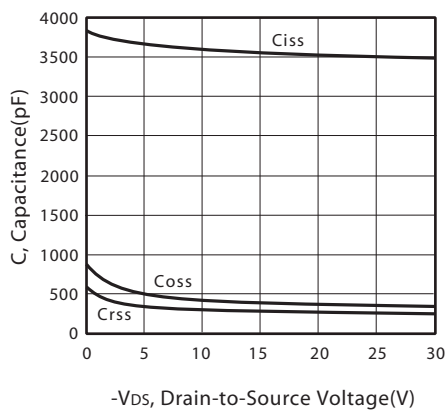
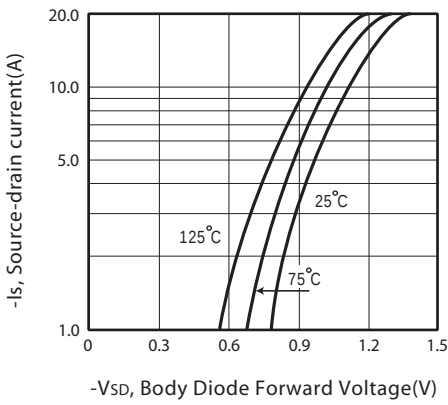
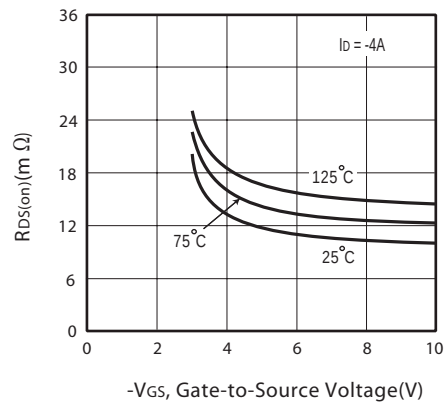
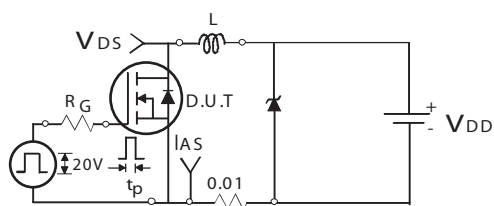


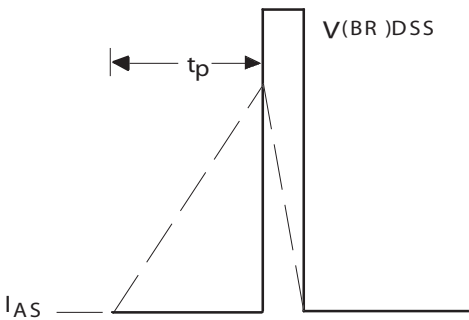
Figure 6. Breakdown Voltage Variation with Temperature





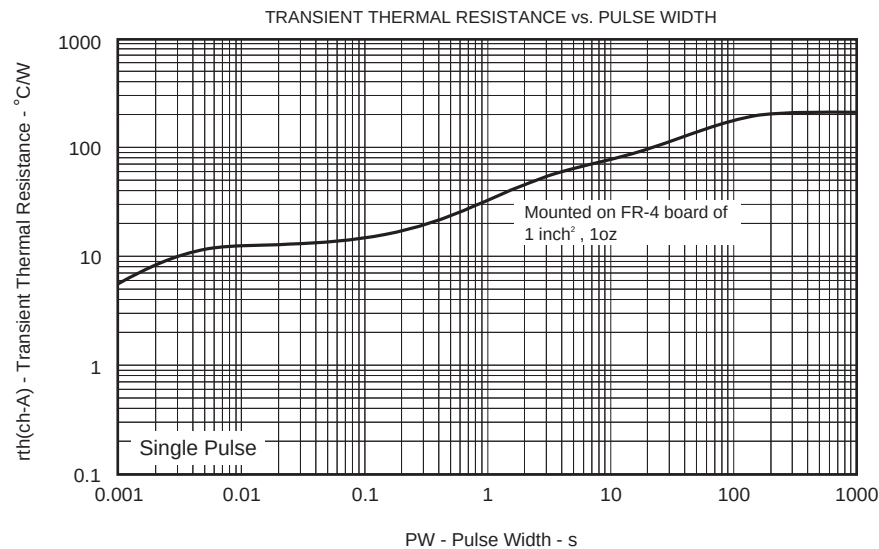
Unclamped Inductive Test Circuit

Figure 13a.



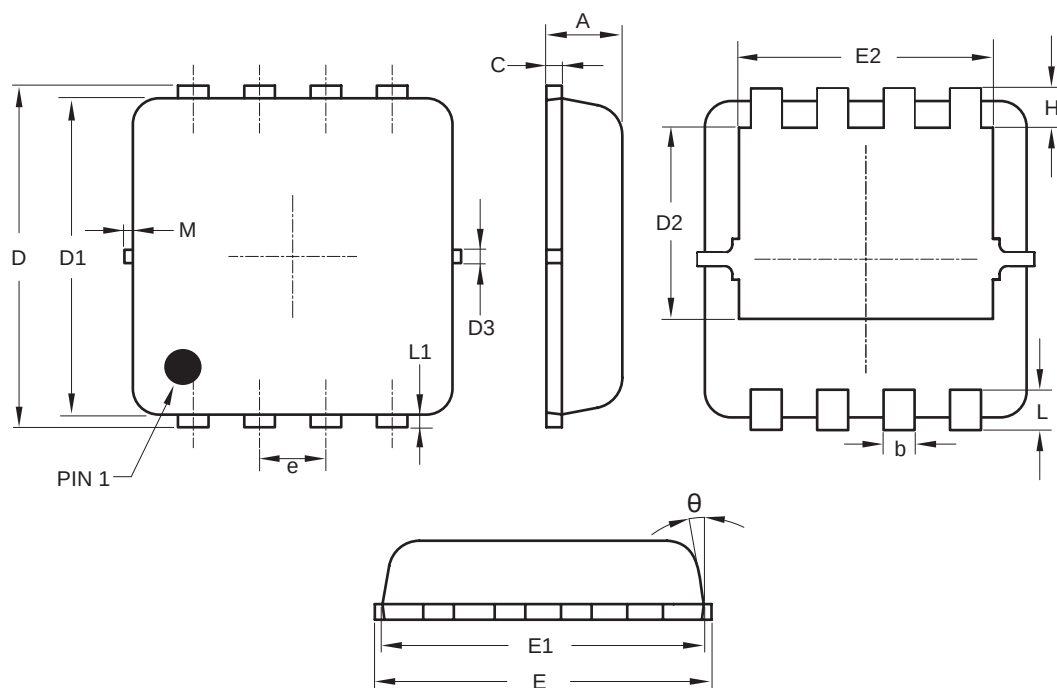
Unclamped Inductive Waveforms

Figure 13b.



## PACKAGE OUTLINE DIMENSIONS

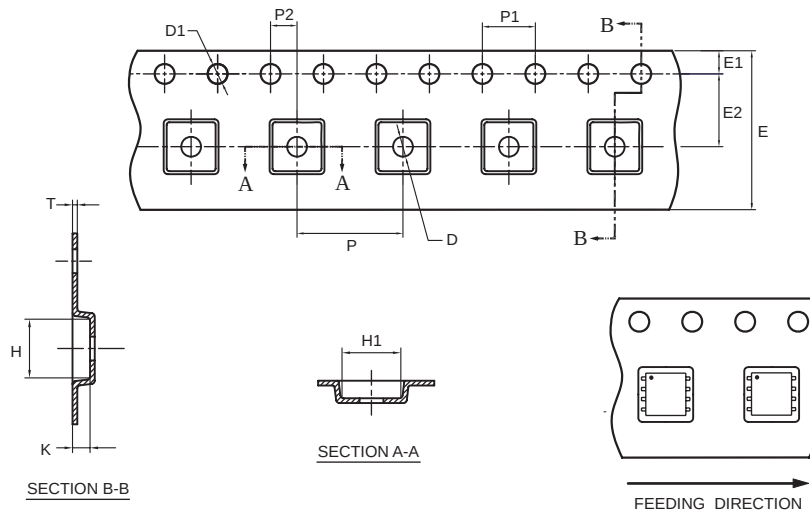
### TSOP 3.3 x 3.3



| SYMBOLS  | MILLIMETERS |      |      |
|----------|-------------|------|------|
|          | MIN.        | NOM. | MAX. |
| A        | 0.70        | 0.75 | 0.80 |
| b        | 0.25        | 0.30 | 0.35 |
| C        | 0.10        | 0.15 | 0.25 |
| D        | 3.25        | 3.35 | 3.45 |
| D1       | 3.00        | 3.10 | 3.20 |
| D2       | 1.78        | 1.88 | 1.98 |
| D3       | —           | 0.13 | —    |
| E        | 3.20        | 3.30 | 3.40 |
| E1       | 3.00        | 3.15 | 3.20 |
| E2       | 2.39        | 2.49 | 2.59 |
| e        | 0.65 BSC    |      |      |
| H        | 0.30        | 0.39 | 0.50 |
| L        | 0.30        | 0.40 | 0.50 |
| L1       | —           | 0.13 | —    |
| M        | —           | —    | 0.15 |
| $\theta$ | —           | 10°  | 12°  |

## TSON 3.3 x 3.3 Tape

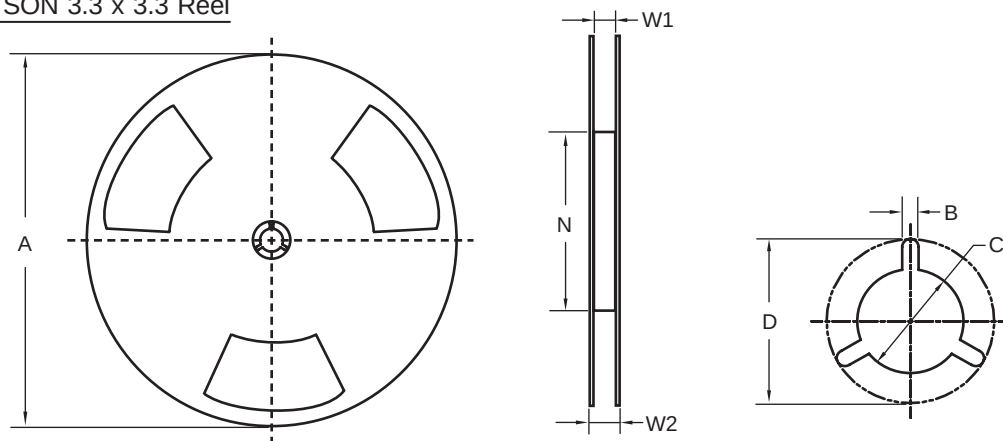
## TSON 3.3 x 3.3 Tape and Reel Data



unit:mm

| PACKAGE  | D                    | D1                             | E                       | E1                 | E2                 | H                  | H1                 | K                  | P                 | P1                | P2                | T                 |
|----------|----------------------|--------------------------------|-------------------------|--------------------|--------------------|--------------------|--------------------|--------------------|-------------------|-------------------|-------------------|-------------------|
| S mini 8 | $\phi 1.50$<br>(MIN) | $\phi 1.50$<br>+0.10<br>- 0.00 | 12.0<br>+0.30<br>- 0.10 | 1.75<br>$\pm 0.10$ | 5.50<br>$\pm 0.05$ | 3.70<br>$\pm 0.10$ | 3.70<br>$\pm 0.10$ | 1.10<br>$\pm 0.10$ | 8.0<br>$\pm 0.10$ | 4.0<br>$\pm 0.10$ | 2.0<br>$\pm 0.05$ | 0.3<br>$\pm 0.05$ |

## TSON 3.3 x 3.3 Reel



UNIT:mm

| TAPE SIZE | REEL SIZE | A             | B                                                        | C                                                                | D          | N                                                        | W1                                                        | W2         |
|-----------|-----------|---------------|----------------------------------------------------------|------------------------------------------------------------------|------------|----------------------------------------------------------|-----------------------------------------------------------|------------|
| 12 mm     | 13 "      | 330 $\pm$ 1.0 | 1.5 $\begin{smallmatrix} +0.5 \\ -0.2 \end{smallmatrix}$ | $\phi 13.0$ $\begin{smallmatrix} +0.5 \\ -0.2 \end{smallmatrix}$ | 20.2(ref.) | 178 $\begin{smallmatrix} +0.0 \\ -2.0 \end{smallmatrix}$ | 12.4 $\begin{smallmatrix} +2.0 \\ -0.0 \end{smallmatrix}$ | 18.4(ref.) |

## TOP MARKING DEFINITION

